L Number	Hits	Search Text	DB	Time stamp
1	43	438/257.CCLS. AND (memory adj cell and	USPAT;	2003/07/13 16:25
-		oxide adj layer and floating adj gate and	US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
		dielectric adj layer and control adj gate)	EPO; JPO;	
		and oxide adj layer with "50" adj	DERWENT	
		angstroms and .25 or quarter adj micron		
	4.0	adj gate	HCDAM.	2003/07/13 16:26
2	43	257/315,316.CCLS. AND 438/257.CCLS. AND (memory adj cell and oxide adj layer and	USPAT; US-PGPUB;	2003/07/13 10:20
		floating adj gate and dielectric adj layer	EPO; JPO;	
		and control adj gate) and oxide adj layer	DERWENT	
	:	with "50" adj angstroms and .25 or quarter		
		adj micron adj gate		
1 -	790596	memory adj cell and oxide adj layer and	USPAT;	2003/07/10 17:09
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control gate	EPO; JPO;	
	1010		DERWENT	2003/07/10 14:38
-	1819	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer	USPAT; US-PGPUB;	2003/07/10 14:36
1		and control adj gate	EPO; JPO;	
		and control adj gate	DERWENT	
_	53	(memory adj cell and oxide adj layer and	USPAT;	2003/07/11 19:01
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and oxide adj layer	EPO; JPO;	
		with "50" adj angstroms	DERWENT	0000/07/10 17 10
-	791060	memory adj cell and oxide adj layer and	USPAT;	2003/07/10 17:10
		floating adj gate and dielectric adj layer	US-PGPUB; EPO; JPO;	
		and control gate	DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/11 19:02
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and oxide adj layer	EPO; JPO;	
		with "50" adj angstroms and .25 adj micron	DERWENT	
		adj gate		2002/07/12 16 6:
-	43		USPAT; US-PGPUB;	2003/07/13 16:24
		floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer	EPO; JPO;	
		with "50" adj angstroms and .25 or quarter	DERWENT	
		adj micron adj gate		
_	l 0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/11 19:04
1		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and oxide adj layer	EPO; JPO;	
		with "50" adj angstroms and (.25 or	DERWENT	
	15	quarter) adj micron (memory adj cell and oxide adj layer and	USPAT;	2003/07/12 11:35
_	15	(memory adj cell and oxide adj layer and   floating adj gate and dielectric adj layer	US-PGPUB;	2000,07,12 11.55
		and control adj gate) and (.25 or quarter)	EPO; JPO;	
		adj micron	DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/11 19:28
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and oxide adj layer	EPO; JPO;	
	1	with "50" adj angstroms and (.25 or	DERWENT	
_	0	quarter) adj micron (memory adj cell and oxide adj layer and	USPAT;	2003/07/12 11:32
-		(memory adj cell and oxide adj layer and   floating adj gate and dielectric adj layer	US-PGPUB;	2000,01,12 11.02
	T T T T T T T T T T T T T T T T T T T	and control adj gate) and oxide adj layer	EPO; JPO;	
		with "50" adj angstroms and (.18 or	DERWENT	
		quarter) adj micron		
-	0	1 1	USPAT;	2003/07/12 11:33
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and oxide adj layer	EPO; JPO;	
		with "50" adj angstroms and (.18) adj	DERWENT	
_	0		USPAT;	2003/07/12 11:33
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and (.18) adj micron	EPO; JPO;	
1	1		DERWENT	
] -	0	1 (	USPAT;	2003/07/12 11:33
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and (.15) adj micron	EPO; JPO; DERWENT	
L	l .		DEVMENT	

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0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.1) adj micron	USPAT; US-PGPUB; EPO; JPO;	2003/07/12

-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12 11:33
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and (.1) adj micron	EPO; JPO;	
			DERWENT	
-	0	(.1) adj micron	USPAT;	2003/07/12 11:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	0	(.18) adj micron	USPAT;	2003/07/12 11:34
		-	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	0	(.25) adj micron	USPAT;	2003/07/12 11:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12 11:35
		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and (.25) adj micron	EPO; JPO;	
			DERWENT	
_	15	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12 11:36
İ		floating adj gate and dielectric adj layer	US-PGPUB;	
		and control adj gate) and (.25 or quarter)	EPO; JPO;	
		adi micron	DERWENT	
_	0	1	USPAT;	2003/07/12 11:36
		floating adj gate and dielectric adj layer	US-PGPUB;	
	1	and control adj gate) and (.25) adj micron	EPO; JPO;	
1			DERWENT	

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